

2N6515 2N6516 2N6517 NPN
2N6518 2N6519 2N6520 PNP

**COMPLEMENTARY SILICON
HIGH VOLTAGE TRANSISTORS**



TO-92 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6515, 2N6518 series devices are complementary silicon transistors designed for high voltage driver and amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage (NPN)
Emitter-Base Voltage (PNP)
Continuous Collector Current
Continuous Base Current
Power Dissipation
Operating and Storage Junction Temperature

| SYMBOL | 2N6515 | 2N6516 | 2N6517 | UNITS |
|----------------|--------|-------------|--------|------------------|
| | 2N6518 | 2N6519 | 2N6520 | |
| V_{CBO} | 250 | 300 | 350 | V |
| V_{CEO} | 250 | 300 | 350 | V |
| V_{EBO} | | 6.0 | | V |
| V_{EBO} | | 5.0 | | V |
| I_C | | 500 | | mA |
| I_B | | 250 | | mA |
| P_D | | 625 | | mW |
| T_J, T_{stg} | | -65 to +150 | | $^\circ\text{C}$ |

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$)

| SYMBOL | TEST CONDITIONS | 2N6515 | | 2N6516 | | 2N6517 | | UNITS |
|---------------|---------------------------------------|--------|--------|--------|--------|--------|------|-------|
| | | 2N6518 | 2N6519 | 2N6519 | 2N6520 | 2N6520 | | |
| I_{CBO} | $V_{CB}=150\text{V}$ | - | 50 | - | - | - | - | nA |
| I_{CBO} | $V_{CB}=200\text{V}$ | - | - | - | 50 | - | - | nA |
| I_{CBO} | $V_{CB}=250\text{V}$ | - | - | - | - | - | 50 | nA |
| I_{EBO} | $V_{EB}=5.0\text{V}$ (NPN) | - | 50 | - | 50 | - | 50 | nA |
| I_{EBO} | $V_{EB}=4.0\text{V}$ (PNP) | - | 50 | - | 50 | - | 50 | nA |
| BV_{CBO} | $I_C=100\mu\text{A}$ | 250 | - | 300 | - | 350 | - | V |
| BV_{CEO} | $I_C=1.0\text{mA}$ | 250 | - | 300 | - | 350 | - | V |
| BV_{EBO} | $I_E=10\mu\text{A}$ (NPN) | 6.0 | - | 6.0 | - | 6.0 | - | V |
| BV_{EBO} | $I_E=10\mu\text{A}$ (PNP) | 5.0 | - | 5.0 | - | 5.0 | - | V |
| $V_{CE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | - | 0.30 | - | 0.30 | - | 0.30 | V |
| $V_{CE(SAT)}$ | $I_C=20\text{mA}, I_B=2.0\text{mA}$ | - | 0.35 | - | 0.35 | - | 0.35 | V |
| $V_{CE(SAT)}$ | $I_C=30\text{mA}, I_B=3.0\text{mA}$ | - | 0.50 | - | 0.50 | - | 0.50 | V |
| $V_{CE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$ | - | 1.0 | - | 1.0 | - | 1.0 | V |
| $V_{BE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | - | 0.75 | - | 0.75 | - | 0.75 | V |
| $V_{BE(SAT)}$ | $I_C=20\text{mA}, I_B=2.0\text{mA}$ | - | 0.85 | - | 0.85 | - | 0.85 | V |
| $V_{BE(SAT)}$ | $I_C=30\text{mA}, I_B=3.0\text{mA}$ | - | 0.90 | - | 0.90 | - | 0.90 | V |
| $V_{BE(ON)}$ | $V_{CE}=10\text{V}, I_C=100\text{mA}$ | - | 2.0 | - | 2.0 | - | 2.0 | V |
| h_{FE} | $V_{CE}=10\text{V}, I_C=1.0\text{mA}$ | 35 | - | 30 | - | 20 | - | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=10\text{mA}$ | 50 | - | 45 | - | 30 | - | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=30\text{mA}$ | 50 | 300 | 45 | 270 | 30 | 200 | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=50\text{mA}$ | 45 | 220 | 40 | 200 | 20 | 200 | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=100\text{mA}$ | 25 | - | 20 | - | 15 | - | |

R2 (18-January 2016)

2N6515 2N6516 2N6517 NPN
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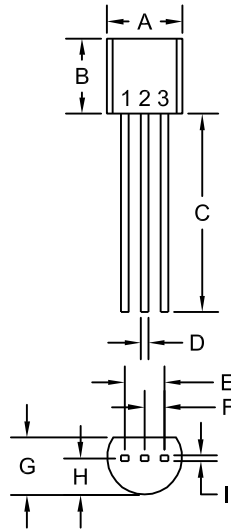
COMPLEMENTARY SILICON
 HIGH VOLTAGE TRANSISTORS



ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|-----------|--|-----|-----|---------------|
| f_T | $V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=20\text{MHz}$ | 40 | 200 | MHz |
| C_{cb} | $V_{CB}=20\text{V}$, $I_E=0$, $f=1.0\text{MHz}$ | | 6.0 | pF |
| C_{eb} | $V_{EB}=0.5\text{V}$, $I_C=0$, $f=1.0\text{MHz}$ (NPN) | | 80 | pF |
| C_{eb} | $V_{EB}=0.5\text{V}$, $I_C=0$, $f=1.0\text{MHz}$ (PNP) | | 100 | pF |
| t_{on} | $V_{CC}=100\text{V}$, $V_{BE}=2.0\text{V}$, $I_C=50\text{mA}$, $I_{B1}=10\text{mA}$ | | 200 | ns |
| t_{off} | $V_{CC}=100\text{V}$, $I_C=50\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$ | | 3.5 | μs |

TO-92 CASE - MECHANICAL OUTLINE



| SYMBOL | DIMENSIONS | | | |
|---------|------------|-------|-------------|------|
| | INCHES | | MILLIMETERS | |
| | MIN | MAX | MIN | MAX |
| A (DIA) | 0.175 | 0.205 | 4.45 | 5.21 |
| B | 0.170 | 0.210 | 4.32 | 5.33 |
| C | 0.500 | - | 12.70 | - |
| D | 0.016 | 0.022 | 0.41 | 0.56 |
| E | 0.100 | | 2.54 | |
| F | 0.050 | | 1.27 | |
| G | 0.125 | 0.165 | 3.18 | 4.19 |
| H | 0.080 | 0.105 | 2.03 | 2.67 |
| I | 0.015 | | 0.38 | |

TO-92 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING:
 FULL PART NUMBER

R1

R2 (18-January 2016)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centalsemi.com

Worldwide Field Representatives:
www.centalsemi.com/wwreps

Worldwide Distributors:
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